Amendments to the Specification:

Please amend paragraph [0003] of the specification as indicated below.

[0003] Force sensors have been produced by various techniques, and include piezoelectric devices, semiconductor devices, capacitive devices and conductive ink film devices. The conductive ink devices typically employ a pair of thin support substrates with one or more conductive ink electrodes on each support substrate facing each other. A force sensitive semiconductive material is deposited over the facing electrodes and the pair of support substrates are bonded to each other. The electrodes are electrically connected to electronic circuitry, which measures the change in resistance or conductivity of the device due to applied force on the support substrates. The conductivity increases with applied force in a determinable manner. Semiconductive materials used in force sensing devices are described in US Patent No. ~~4,856,933~~ 4,856,993 and US Patent No. 5,296,837. The use of particulate conductive materials in force sensors are also described in US Patent No. ~~5,302936~~ 5,302,936. A force sensor may be made by depositing a semiconductive ink by spraying or silk screening a thin layer onto a pair of flexible support substrates having conductive electrodes. When the ink dries, the pair of support substrates are bonded together to form a force sensor. However, force sensors manufactured by this method have a conductance that increases with temperature. Extensive testing of force sensors has shown a significant shift in the sensitivity of the device with temperature. Although it is possible to compensate for these effects through conditioning electronics, the task would be greatly simplified by finding a resistive temperature device which ideally matches the shift in sensitivity of the force sensor.